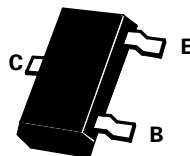


# SOT23 PNP SILICON PLANAR HIGH VOLTAGE TRANSISTOR

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## HT3

PARTMARKING DETAIL - 3T



### ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Collector-Base Voltage	$V_{CBO}$	-90	V
Collector-Emitter Voltage	$V_{CEO}$	-80	V
Emitter-Base Voltage	$V_{EBO}$	-5	V
Continuous Collector Current	$I_C$	-100	mA
Power Dissipation at $T_{amb} = 25^\circ\text{C}$	$P_{tot}$	330	mW
Operating and Storage Temperature Range	$T_j; T_{stg}$	-55 to +150	$^\circ\text{C}$

### ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^\circ\text{C}$ ).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Collector-Base Breakdown Voltage	$V_{(BR)CBO}$	-90		V	$I_C = -10\mu\text{A}$
Collector-Emitter Breakdown Voltage	$V_{(BR)CEO}$	-80		V	$I_C = -2\text{mA}$
Emitter-Base Breakdown Voltage	$V_{(BR)EBO}$	-5		V	$I_E = -10\mu\text{A}$
Collector Cut-Off Current	$I_{CBO}$		-100	nA	$V_{CB} = -80\text{V}, I_E = 0$
	$I_{CES}$		-100 -5	nA $\mu\text{A}$	$V_{CE} = -80\text{V}, V_{BE} = 0$ $V_{CE} = -80\text{V}, V_{BE} = 0$ $T_j = 125^\circ\text{C}$
	$I_{CEX}$		-10	$\mu\text{A}$	$V_{CE} = -80\text{V}, V_{BE} = -0.2\text{V}, T_j = 85^\circ\text{C}$
Emitter Cut-Off Current	$I_{EBO}$		-200	nA	$V_{EB} = -4\text{V}$
Static Forward Current Transfer Ratio	$h_{FE}$	30 35 50 30			$I_C = -100\mu\text{A}, V_{CE} = -1\text{V}$ $I_C = -1\text{mA}, V_{CE} = -1\text{V}$ $I_C = -10\text{mA}, V_{CE} = -1\text{V}$ $I_C = -50\text{mA}, V_{CE} = -1\text{V}$
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$		-750	mV	$I_C = -50\text{mA}, I_B = -5\text{mA}$
Base-Emitter Saturation Voltage	$V_{BE(sat)}$		-1.1	V	$I_C = -50\text{mA}, I_B = -5\text{mA}$
Output Capacitance	$C_{obo}$		10	pF	$V_{CB} = -10\text{V}, I_E = 0, f = 1\text{MHz}$
Transition Frequency	$f_T$	50		MHz	$I_C = -10\text{mA}, V_{CE} = -5\text{V}$ $f = 10\text{MHz}$
Switching Times	$t_{on}$		500	ns	$I_C = -10\text{mA}$ ,
	$t_{off}$		1000	ns	$I_{B1} = I_{B2} = -1\text{ma}$

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